

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in plastic TO-92 variants, primarily intended for low-noise input stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment.

QUICK REFERENCE DATA

	BC549	BC550
Collector-emitter voltage ($V_{BE} = 0$)	max 30	50 V
Collector-emitter voltage (open base)	max 30	45 V
Collector current (peak value)	max 200	200 mA
Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$	max 500	500 mW
Junction temperature	max 150	150 $^{\circ}\text{C}$
Small-signal current gain		
$I_C = 2\text{ mA}$; $V_{CE} = 5\text{ V}$; $f = 1\text{ kHz}$	$h_{fe} >$	240
	$h_{fe} <$	900
Transition frequency		
$I_C = 10\text{ mA}$; $V_{CE} = 5\text{ V}$	f_T typ	300 MHz
Note figure at $R_S = 2\text{ k}\Omega$		
$I_C = 200\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$	F typ	1,4 dB
$f = 30\text{ Hz to }15\text{ kHz}$	$F <$	3 dB
$f = 1\text{ kHz}$; $B = 200\text{ Hz}$	F typ	1 dB
$f = 10\text{ Hz to }50\text{ Hz}$ (equivalent noise voltage)	$V_n <$	0,135 μV

MECHANICAL DATA

Fig. 1 TO-92 variant.

Dimensions in mm

